ABSTRACT OF THE DISCLOSURE

0028 Maximizing a common process window for optical proximity correction (OPC)-modified features of a semiconductor design having varying pitch is disclosed. For each pitch within a semiconductor design, a bias needed at the pitch that maximizes a common process window for the number of pitches given a critical dimension (CD) specification for a semiconductor design of the photomask is determined. The original layout for the semiconductor design of the photomask is then modified by performing rule-based optical-proximity correction (OPC), including adding the bias determined at each pitch, to yield a modified layout for the semiconductor design of the photomask. The modified layout is further modified by performing model-based on the modified layout such that exposed semiconductor wafer CD's at each pitch are at least substantially equal to the CD specification for the pitch, to yield a final layout for the semiconductor design of the photomask.